Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- · Logic-level compatible
- · Very fast switching
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- · Relay driver
- · High-speed line driver
- · High-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-30	V	
V_{GS}	gate-source voltage			-20	-	20	V	
I _D	drain current	$V_{GS} = -10 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-	-6	Α	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -10 V; I_D = -4.6 A; T_j = 25 °C		-	35	45	mΩ	

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Symbol	Description	Simplified outline	Graphic symbol
D	drain	<u> </u>	D -
D	drain		
G	gate	0 H1 H2 H3	G \downarrow
S	source	TSOP6 (SOT457)	
D	drain		
D	drain		S 017aaa259
	D D S D	D drain D drain G gate S source D drain	D drain D drain G gate S source TSOP6 (SOT457) D drain

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMN50EPE	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMN50EPE	3L

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-6	Α
		V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-4.6	Α
		V _{GS} = -10 V; T _{amb} = 100 °C	[1]	-	-2.9	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-19	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	560	mW
			[1]	-	1.4	W
		T _{sp} = 25 °C		-	6.25	mW
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	diode				<u>'</u>	
I _S	source current	T _{amb} = 25 °C	[1]	-	-1.4	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

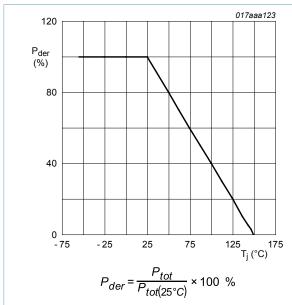


Fig. 1. Normalized total power dissipation as a function of junction temperature

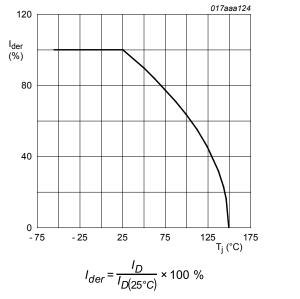


Fig. 2. Normalized continuous drain current as a function of junction temperature

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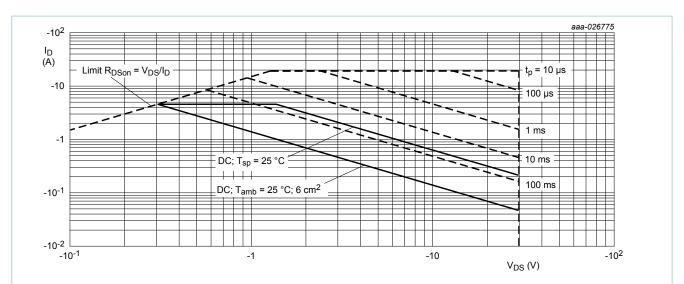


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient		[1]	-	195	225	K/W
			[2]	-	78	90	K/W
		in free air; t ≤ 5 s	[2]	-	55	63	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	15	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

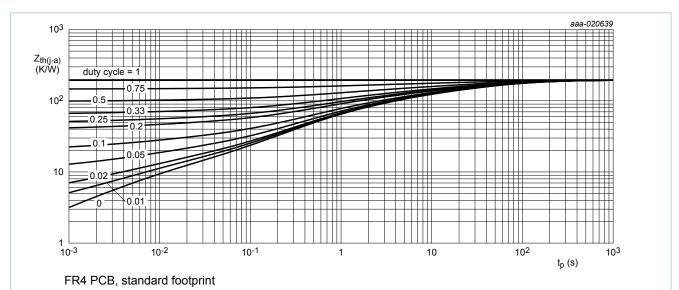


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

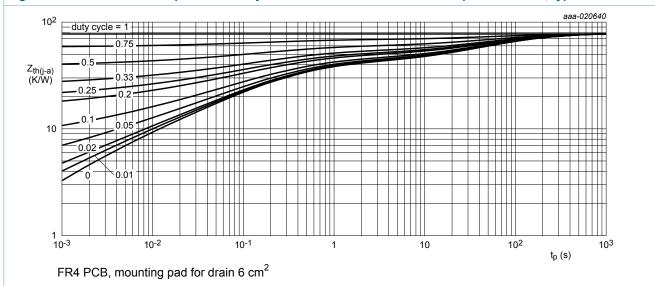


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			,
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-1	-2	-3	V
I _{DSS}	drain leakage current	$V_{DS} = -30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-1	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	10	μΑ
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-10	μA
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-2	μΑ
Doon	drain-source on-state	V_{GS} = -10 V; I_D = -4.6 A; T_j = 25 °C	-	35	45	mΩ
	resistance	V _{GS} = -10 V; I _D = -4.6 A; T _j = 150 °C	-	51	67	mΩ
		V_{GS} = -4.5 V; I_D = -3.6 A; T_j = 25 °C	-	49	72	mΩ
9fs	forward transconductance	V_{DS} = -10 V; I_{D} = -4.6 A; T_{j} = 25 °C	-	14.2	-	S
R _G	gate resistance	f = 1 MHz	-	13	-	Ω
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -15 V; I_{D} = -4.2 A; V_{GS} = -10 V;	-	12.8	20	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	2.2	-	nC
Q _{GD}	gate-drain charge		-	2.2	-	nC
C _{iss}	input capacitance	V _{DS} = -15 V; f = 1 MHz; V _{GS} = 0 V;	-	793	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	134	-	pF
C _{rss}	reverse transfer capacitance		-	84	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = -15 \text{ V}; I_D = -4.2 \text{ A}; V_{GS} = -10 \text{ V};$	-	6	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	19	-	ns
t _{d(off)}	turn-off delay time		-	36	-	ns
t _f	fall time		-	19	-	ns
Source-dra	in diode		'		,	,
V _{SD}	source-drain voltage	I_S = -1.4 A; V_{GS} = 0 V; T_j = 25 °C	-	-0.8	-1.2	V

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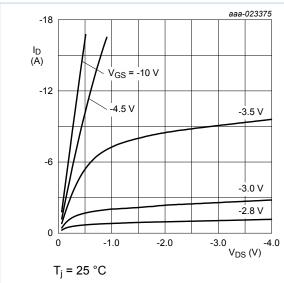


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

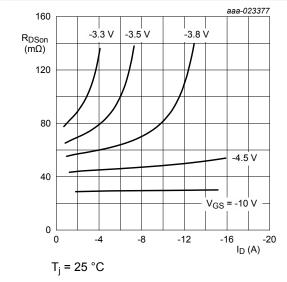


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

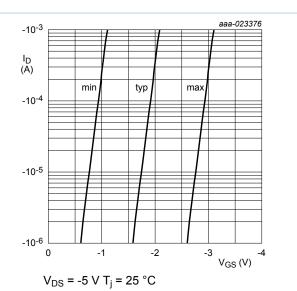


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

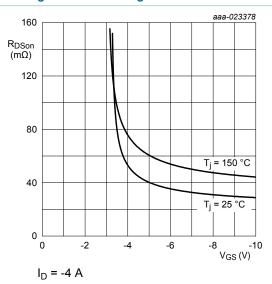


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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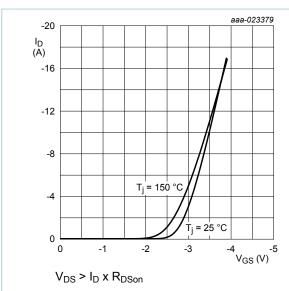


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

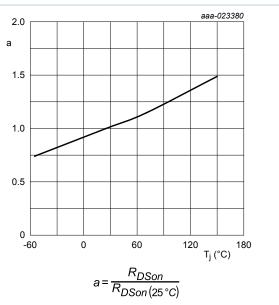


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

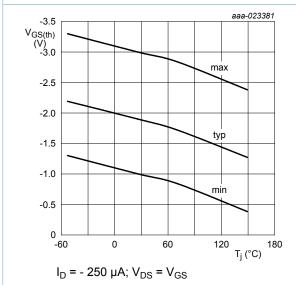


Fig. 12. Gate-source threshold voltage as a function of junction temperature

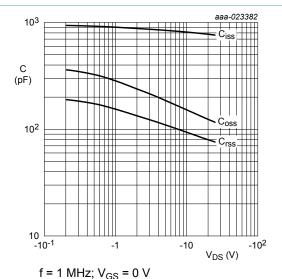


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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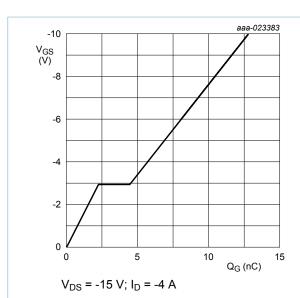


Fig. 14. Gate-source voltage as a function of gate charge; typical values

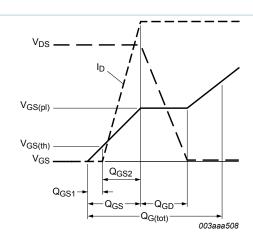


Fig. 15. Gate charge waveform definitions

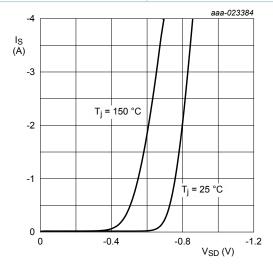
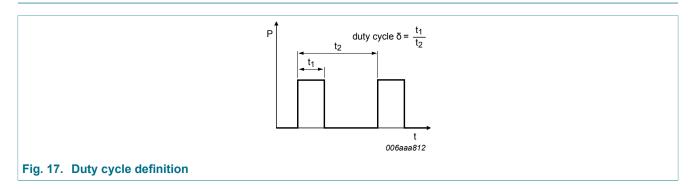


Fig. 16. Source current as a function of source-drain voltage; typical values

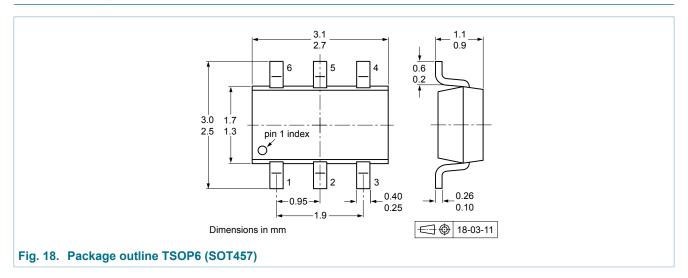
 $V_{GS} = 0 V$

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11. Test information

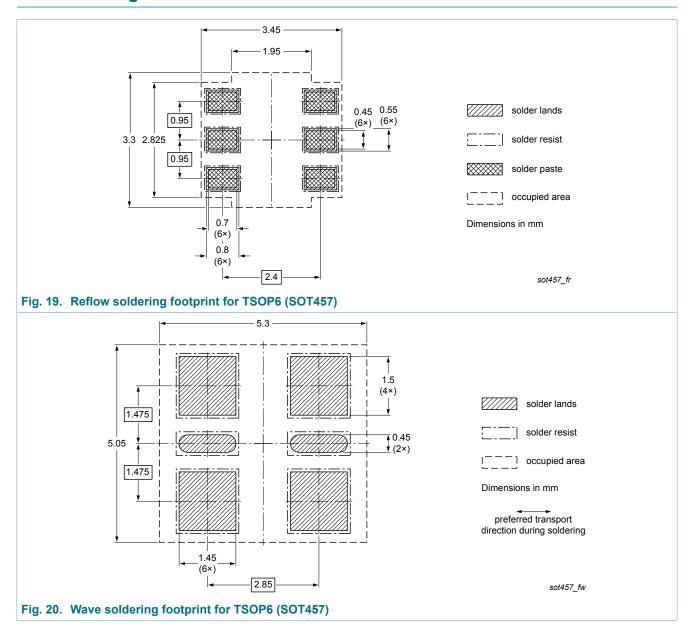


12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMN50EPE v.1	20180416	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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